

Device Features

- OIP3 = 44.0 dBm @ 70 MHz
- Gain = 20.3 dB @ 70 MHz
- Output P1 dB = 23.5 dBm @ 70 MHz
- 50 Ω Cascadable
- Patented over voltage protection
- Lead-free/RoHS-compliant SOT-89 SMT package



Product Description

BeRex's BIF3 is a high performance InGaP/GaAs HBT MMIC amplifier, internally matched to 50 Ohms and uses a patented **over voltage protection** circuit to protect a internal device. The BIF3 is designed for high linearity IF amplifier that requires excellent gain, high OIP3 and flatness. It is packaged in a RoHS-compliant with SOT-89 surface mount package.

Typical Performance¹

Parameter	Frequency					Unit
	70	140	250	500	800	
Gain	20.3	20.2	19.9	19.0	17.9	dB
S11	-19.0	-18.0	-15.0	-11.0	-8.0	dB
S22	-16.0	-17.0	-16.0	-13.0	-11.0	dB
OIP3 ²	44.0	41.5	40.5	40.5	39.5	dBm
P1dB	23.5	24.5	24.5	24.2	24.0	dBm
Noise Figure	5.1	5.2	5.2	5.3	5.3	dB

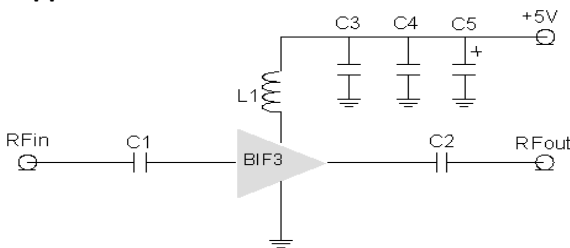
¹ Device performance _ measured on a BeRex evaluation board at 25°C, 50 Ω system.

² OIP3 _ measured with two tones at an output of 8 dBm per tone separated by 1 MHz.

Applications

- Base station Infrastructure/RFID
- Commercial/Industrial/Military wireless system

Applications Circuit



*C1, C2=8200pF \pm 5%; C3 = 100 pF \pm 5%; C4 = 1000pF \pm 5%

*C5 = 10uF; L1 = 680nH \pm 5%

	Min.	Typical	Max.	Unit
Bandwidth	5		800	MHz
I _c @ (V _c = 5V)	75	85	97	mA
V _c		5.0		V
dG/dT		-0.004		dB/°C
R _{TH}		45		°C/W

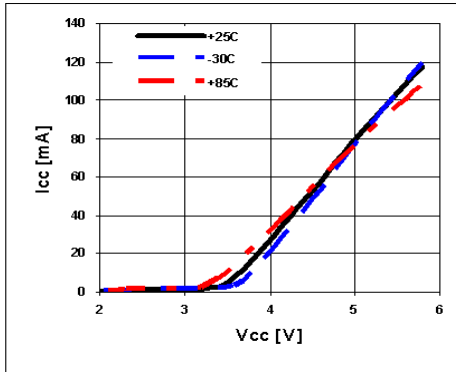
Absolute Maximum Ratings

Parameter	Rating	Unit
Operating Case Temperature	-40 to +85	°C
Storage Temperature	-55 to +155	°C
Junction Temperature	+220	°C
Operating Voltage	+7.0	V
Supply Current	140	mA
Input RF Power	23	dBm

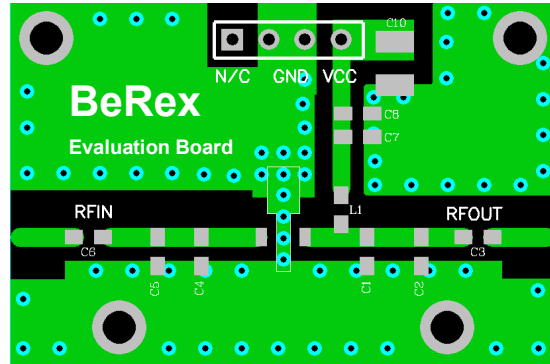
Operation of this device above any of these parameters may result in permanent damage.

Above 7V, a device goes to protection mode.

V-I Characteristics



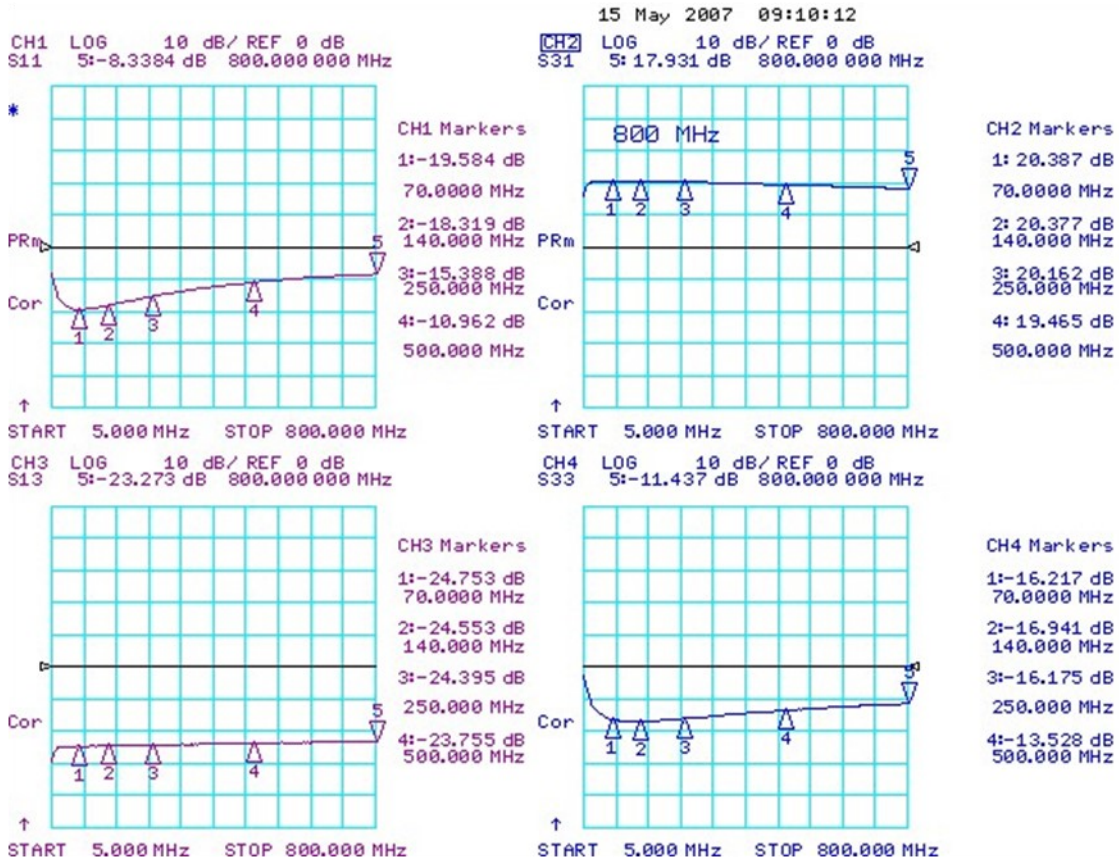
BeRex SOT89 Evaluation Board



*Dielectric constant _ 4.2 *RF pattern width 52mil *31mil thick FR4 PCB

Typical Device Data

S-parameters (Vc=5V, Ic=80mA, T=25°C)



S-Parameter

 (V_{device} = 5.0V, I_{cc} = 85mA, T = 25 °C, calibrated to device leads)

Freq [MHz]	S11 [Mag]	S11 [Ang]	S21 [Mag]	S21 [Ang]	S12 [Mag]	S12 [Ang]	S22 [Mag]	S22 [Ang]
100	0.624	178.2	10.523	169.9	0.059	1.5	0.096	-26.0
500	0.678	164.5	7.809	137.3	0.069	0.3	0.162	-107.1
1000	0.748	144.2	5.812	155.4	0.067	-0.4	0.223	-156.6
1500	0.788	121.2	4.823	100.6	0.078	-7.1	0.272	167.3
2000	0.790	102.1	4.095	82.6	0.070	-23.9	0.271	140.3
2500	0.861	76.9	3.935	74.1	0.076	-17.5	0.305	116.8
3000	0.873	54.1	4.121	51.6	0.072	-41.4	0.327	94.2
3500	0.955	26.4	3.614	30.1	0.061	-39.1	0.347	75.9
4000	1.037	-3.3	3.252	11.4	0.060	-53.2	0.362	55.0

 Typical Performance (V_d = 5V, I_c = 85mA, T = 25°C)

Freq	MHz	70	140	250	500	800
S21	dB	20.3	20.2	19.9	19.0	17.9
S11	dB	-19	-18	-15	-11	-8
S22	dB	-16	-17	-16	-13	-11
P1	dBm	23.5	24.5	24.5	24.2	24.0
OIP3	dBm	44	41.5	40.5	40.5	39.5
NF	dB	5.1	5.2	5.2	5.3	5.3

 Typical Performance (V_d = 4.7V, I_c = 64mA, T = 25°C)

Freq	MHz	70	140	250	500	800
S21	dB	20.1	19.9	19.7	18.9	17.6
S11	dB	-27.2	-24.6	-16.8	-11.3	-9.3
S22	dB	-13.1	-12.6	-13	-12.5	-9.7
P1	dBm	22.9	23.5	23.3	23.3	22.7
OIP3	dBm	35.0	38.5	39.5	36.5	35.3
NF	dB	5.1	5.2	5.2	5.3	5.3

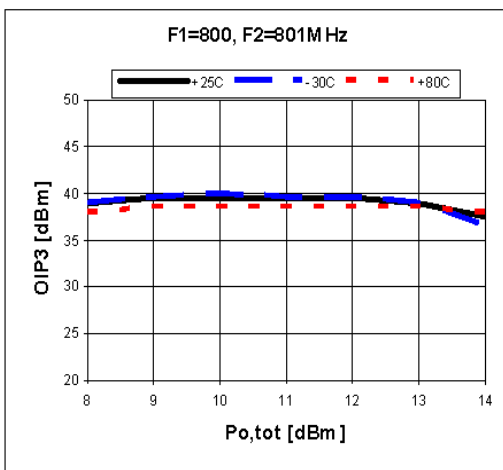
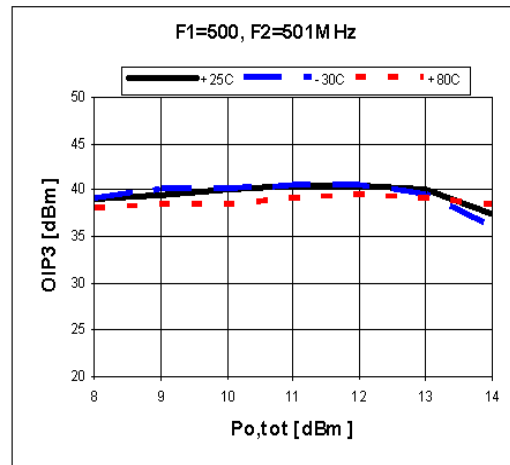
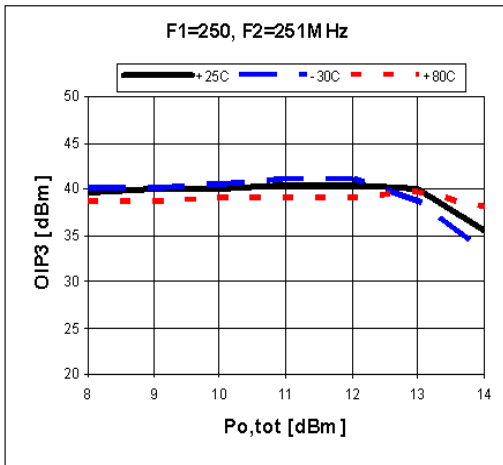
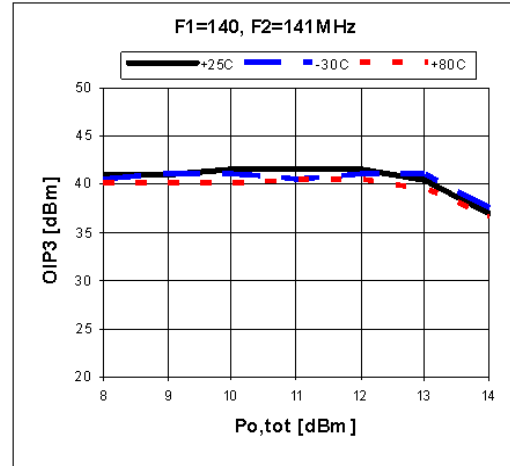
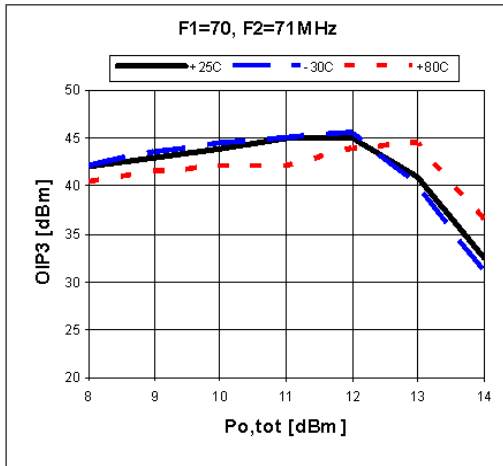
 Typical Performance (V_d = 4.5V, I_c = 54mA, T = 25°C)

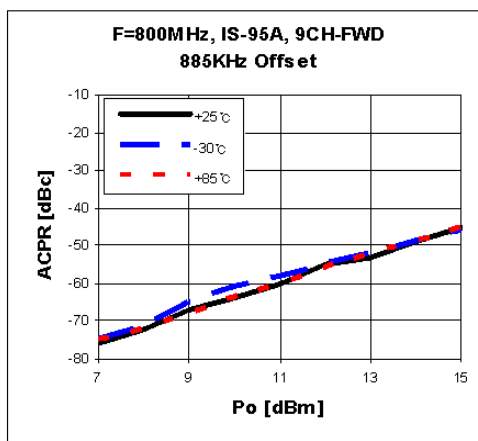
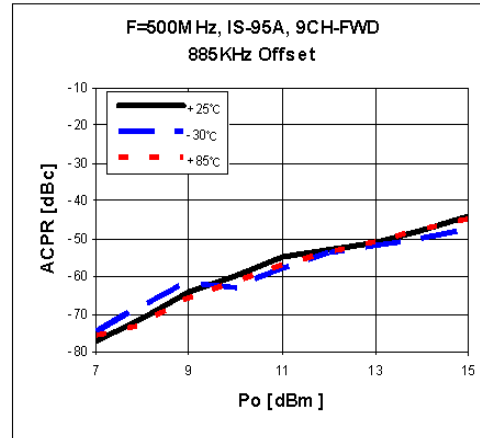
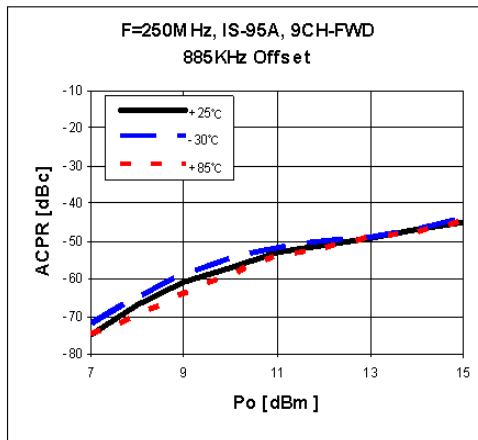
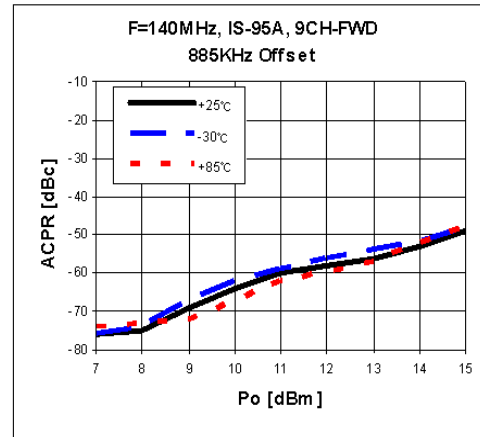
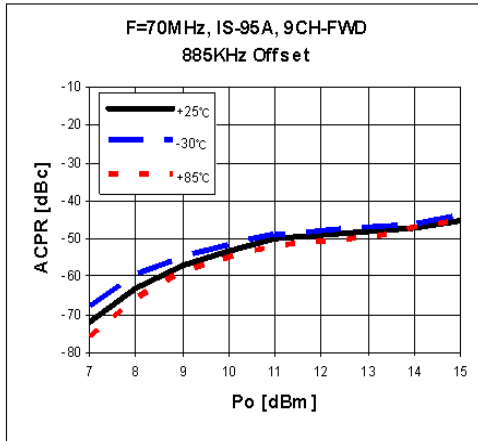
Freq	MHz	70	140	250	500	800
S21	dB	20.2	20.2	19.8	18.7	17.5
S11	dB	-18.8	-19	-16.1	-11.8	-9.2
S22	dB	-14.1	-16	-15.1	-11.8	-9.6
P1	dBm	22.1	23.0	23.1	22.6	22.2
OIP3	dBm	34.5	37.5	34.5	35.5	34.5
NF	dB	5.1	5.2	5.2	5.3	5.3

5-800 MHz Internally Matched IF Amplifier

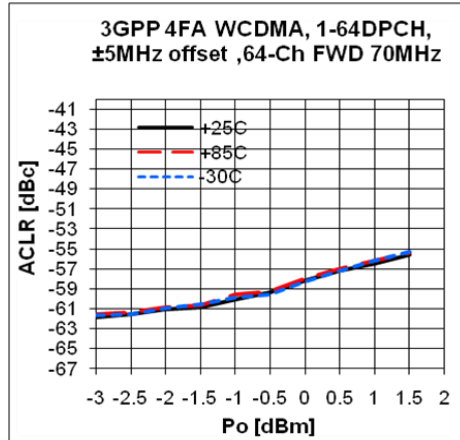
Typical Performance (Vd = 4V, Ic = 28mA, T = 25°C)

Freq	MHz	70	140	250	500	800
S21	dB	19.5	19.4	19.1	18.1	16.8
S11	dB	-18.4	-18.5	-15.8	-11.5	-8.9
S22	dB	-12.3	-13.8	-13.5	-11.3	-9.4
P1	dBm	20.7	21.2	21.2	20.7	13.5
OIP3	dBm	35	29	27.5	25.5	31
NF	dB	5.1	5.2	5.2	5.3	5.3

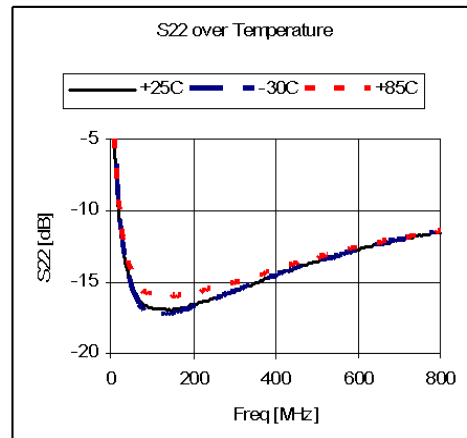
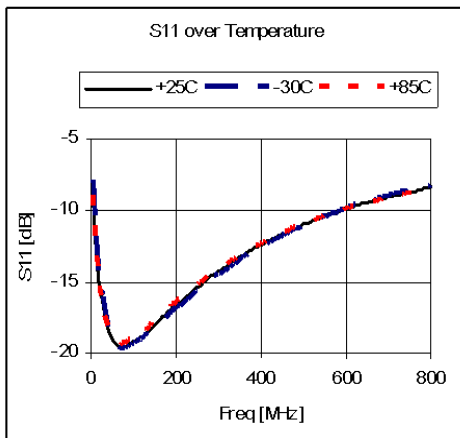
Device Performance
OIP3


ACPR


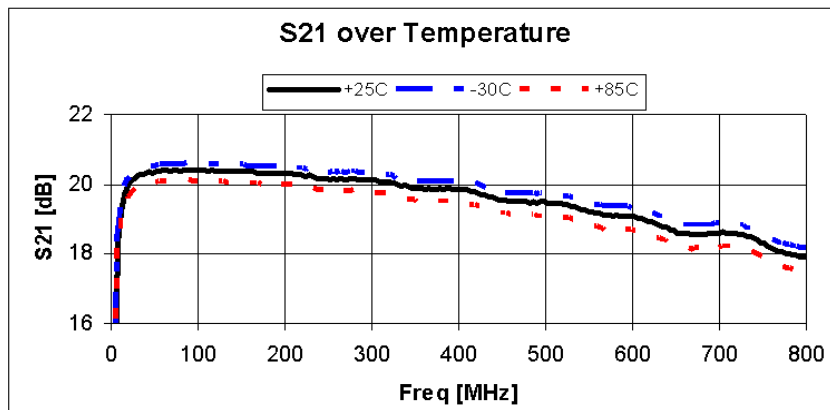
ACLR



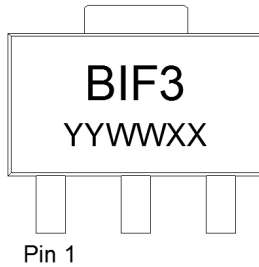
S-Parameters(S11/S22)



Gain Flatness

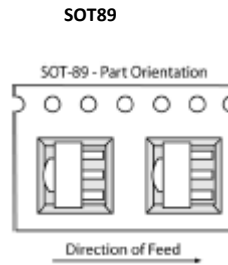


Package Marking



YY = Year, WW = Working Week,
XX = Wafer No.

Tape & Reel



Packaging information:

Tape Width (mm): 12
Reel Size (inches): 7
Device Cavity Pitch (mm): 8
Devices Per Reel: 1000

Lead plating finish

100% Tin Matte finish

(All BeRex products undergoes a 1 hour, 150 degree C, Anneal bake to eliminate thin whisker growth concerns.)

MSL / ESD Rating

ESD Rating:	Class 1C
Value:	Passes <2000V
Test:	Human Body Model (HBM)
Standard:	JEDEC Standard JESD22-A114B
MSL Rating:	Level 1 at +265°C convection reflow
Standard:	JEDEC Standard J-STD-020



Proper ESD procedures should be followed when handling this device.

NATO CAGE code:

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